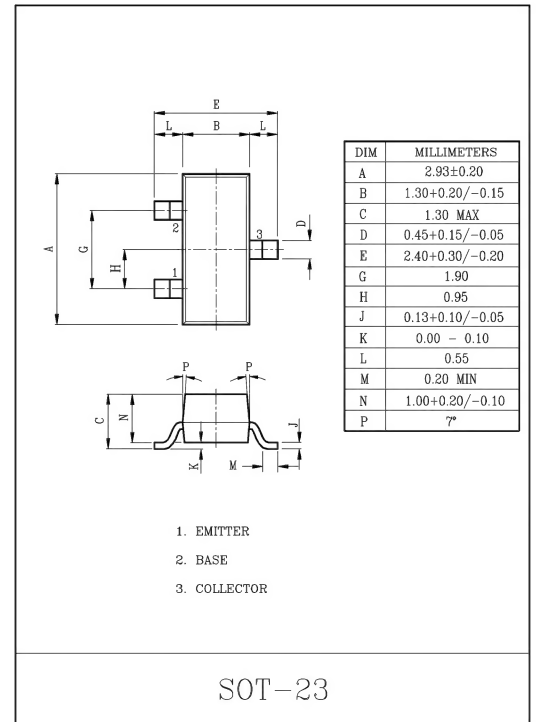
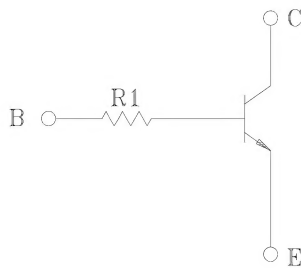


SWITCHING APPLICATION.
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

FEATURES

- With Built-in Bias Resistors.
- Simplify Circuit Design.
- Reduce a Quantity of Parts and Manufacturing Process.

EQUIVALENT CIRCUIT



MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

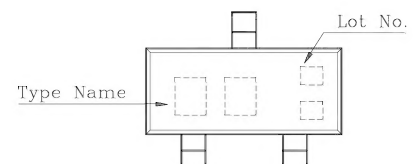
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I _{CBO}	V _{CB} =50V, I _E =0	–	–	100	nA
Emitter Cut-off Current		I _{EBO}	V _{EB} =5V, I _C =0	–	–	100	nA
DC Current Gain		h _{FE}	V _{CE} =5V, I _C =1mA	120	–	–	
Collector-Emitter Saturation Voltage		V _{CE(sat)}	I _C =10mA, I _B =0.5mA	–	0.1	0.3	V
Transition Frequency		f _T *	V _{CE} =10V, I _C =5mA	–	250	–	MHz
Input Resistor	KRC110S	R ₁		–	4.7	–	k Ω
	KRC111S			–	10	–	
	KRC112S			–	100	–	
	KRC113S			–	22	–	
	KRC114S			–	47	–	

Note : * Characteristic of Transistor Only

MARK SPEC

TYPE	KRC110S	KRC111S	KRC112S	KRC113S	KRC114S
MARK	NK	NM	NN	NO	NP

Marking



KRC110S ~ KRC114S

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC			SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Switching Time	Rise Time	KRC110S	t_r	$V_O=5V$ $V_{IN}=5V$ $R_L=1k\Omega$	-	0.025	-	μS
		KRC111S			-	0.03	-	
		KRC112S			-	0.3	-	
		KRC113S			-	0.06	-	
		KRC114S			-	0.11	-	
	Storage Time	KRC110S	t_{stg}		-	3.0	-	
		KRC111S			-	2.0	-	
		KRC112S			-	6.0	-	
		KRC113S			-	4.0	-	
		KRC114S			-	5.0	-	
	Fall Time	KRC110S	t_f		-	0.2	-	
		KRC111S			-	0.12	-	
		KRC112S			-	2.0	-	
		KRC113S			-	0.9	-	
		KRC114S			-	1.4	-	